

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Single high-speed switching diode, fabricated in planar technology, and encapsulated in a small hermetically sealed glass SOD80C Surface-Mounted Device (SMD) package.

### 1.2 Features

■ High switching speed:  $t_{rr} \le 4$  ns

Reverse voltage: V<sub>R</sub> ≤ 75 V

Repetitive peak reverse voltage: V<sub>RRM</sub> ≤ 100 V
 Repetitive peak forward current: I<sub>FRM</sub> ≤ 450 mA

Small hermetically sealed glass SMD package

### 1.3 Applications

- High-speed switching
- Reverse polarity protection

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current		<u>[1]</u> _	-	200	mA
I <sub>FRM</sub>	repetitive peak forward current		-	-	450	mA
$V_R$	reverse voltage		-	-	75	V
V <sub>F</sub>	forward voltage	$I_F = 100 \text{ mA}$	-	-	1000	mV
t <sub>rr</sub>	reverse recovery time		[2]	-	4	ns

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] When switched from  $I_F = 10$  mA to  $I_R = 10$  mA;  $R_L = 100$   $\Omega$ ; measured at  $I_R = 1$  mA.



### **High-speed switching diode**

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	
2	anode	k	1 2
			006aab040

<sup>[1]</sup> The marking band indicates the cathode.

## 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BAS32L	-	hermetically sealed glass surface-mounted package; 2 connectors	SOD80C			

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BAS32L	marking band

<sup>[1]</sup> black: made in Philippines brown: made in China

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	100	V
$V_R$	reverse voltage		-	75	V
I <sub>F</sub>	forward current		<u>[1]</u> _	200	mA
I <sub>FRM</sub>	repetitive peak forward current		-	450	mA
$I_{FSM}$	non-repetitive peak forward	square wave	[2]		
	current	$t_p = 1 \mu s$	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		$t_p = 1 s$	-	0.5	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} = 25  ^{\circ}C$	<u>[1]</u> _	500	mW

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### **High-speed switching diode**

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	200	°C
T <sub>amb</sub>	ambient temperature		-65	+200	°C
T <sub>stg</sub>	storage temperature		-65	+200	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	350	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	300	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 7. Characteristics

**Table 7. Characteristics** 

T<sub>amb</sub> = 25 °C unless otherwise specified.

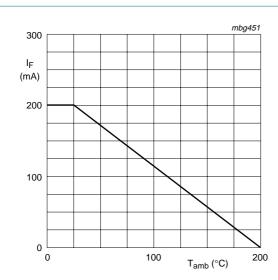
	-					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	$I_F = 5 \text{ mA}$	620	-	750	mV
		I <sub>F</sub> = 100 mA	-	-	1000	mV
		$I_F = 100 \text{ mA}; T_j = 100 ^{\circ}\text{C}$	-	-	930	mV
I <sub>R</sub>	forward voltage  reverse current  diode capacitance reverse recovery time	V <sub>R</sub> = 20 V	-	-	25	nA
		V <sub>R</sub> = 75 V	-	-	5	μΑ
		$V_R = 20 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
		$V_R = 75 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 0 V; f = 1 MHz$	-	-	2	pF
t <sub>rr</sub>			<u>[1]</u> -	-	4	ns
$V_{FR}$	•		[2] _	-	2.5	V

<sup>[1]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega;$  measured at  $I_R$  = 1 mA.

<sup>[2]</sup>  $T_i = 25$  °C prior to surge.

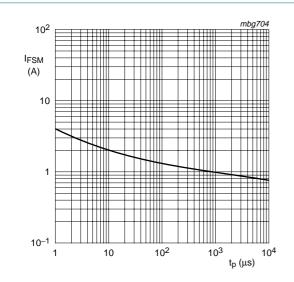
<sup>[2]</sup> When switched from  $I_F = 50$  mA;  $t_r = 20$  ns.

### **High-speed switching diode**



FR4 PCB, standard footprint

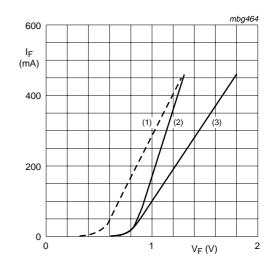
Fig 1. Forward current as a function of ambient temperature; derating curve



Based on square wave currents.

T<sub>i</sub> = 25 °C prior to surge

Fig 3. Non-repetitive peak forward current as a function of pulse duration; maximum values

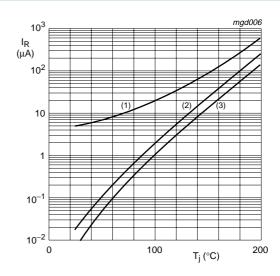


(1)  $T_j = 175$  °C; typical values

(2)  $T_i = 25 \,^{\circ}C$ ; typical values

(3)  $T_i = 25 \,^{\circ}C$ ; maximum values

Fig 2. Forward current as a function of forward voltage



(1)  $V_R = 75 \text{ V}$ ; maximum values

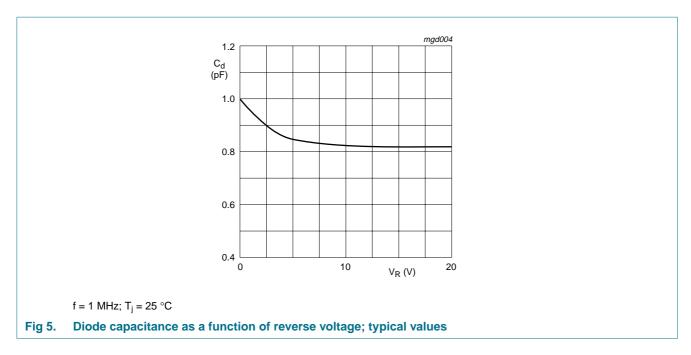
(2) V<sub>R</sub> = 75 V; typical values

(3)  $V_R = 20 \text{ V}$ ; typical values

Fig 4. Reverse current as a function of junction temperature

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### High-speed switching diode



### 8. Test information

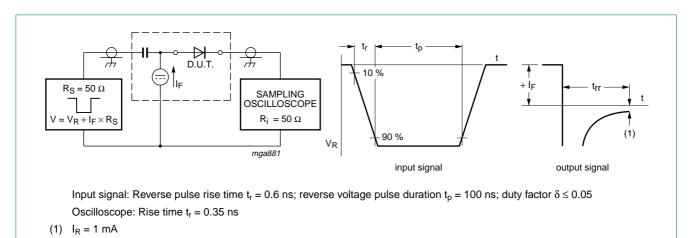
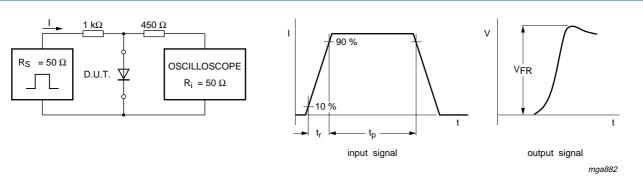


Fig 6. Reverse recovery time test circuit and waveforms



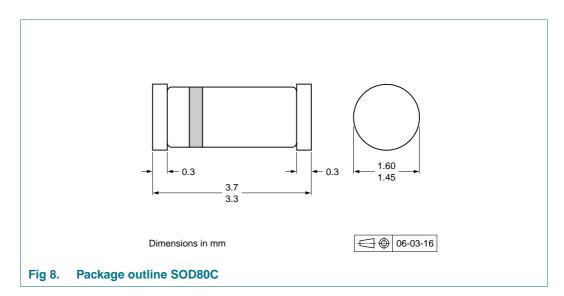
Input signal: Forward pulse rise time  $t_r$  = 20 ns; forward current pulse duration  $t_p \ge 100$  ns; duty factor  $\delta \le 0.005$ 

Fig 7. Forward recovery voltage test circuit and waveforms

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**High-speed switching diode** 

## 9. Package outline



# 10. Packing information

Table 8. Packing methods

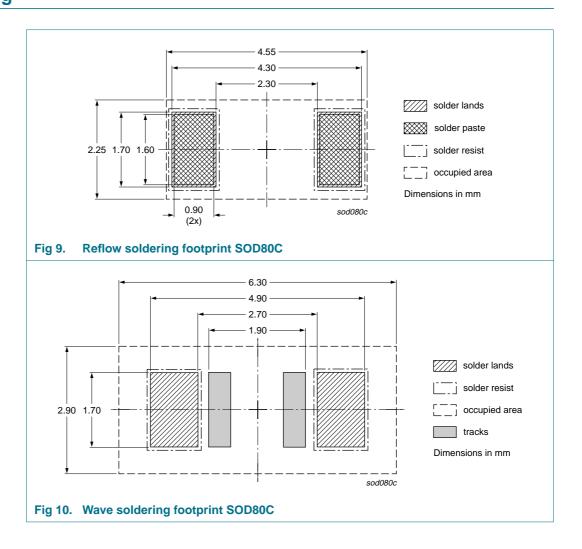
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qua	intity
			2500	10000
BAS32L	SOD80C	4 mm pitch, 8 mm tape and reel	-115	-135

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

### **High-speed switching diode**

## 11. Soldering



### High-speed switching diode

# 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS32L_6	20081029	Product data sheet	-	BAS32L_5
Modifications:	• Figure 8: am	ended		
	<ul> <li>Section 13 "L</li> </ul>	<u>egal information</u> ": updated		
BAS32L_5	20080103	Product data sheet	-	BAS32L_4
BAS32L_4	20050322	Product data sheet	-	BAS32L_3
BAS32L_3	20020123	Product specification	-	BAS32L_2
BAS32L_2	19960910	Product specification	-	BAS32L_1
BAS32L_1	19960423	Product specification	-	-

### **High-speed switching diode**

### 13. Legal information

### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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